

ABSTRACT

A group III nitride substrate manufacturing apparatus according to the present invention includes: a rotating susceptor (3) for holding and rotating a seed crystal (2) in a reaction container (1); a heating means (9) for heating the seed crystal (2); a revolving susceptor (4) for placing thereon and revolving the rotating susceptor (3); a first gas ejection port (6) for ejecting a gas of a chloride of a group III element at a predetermined angle with respect to the direction of the axis of rotation of the revolving susceptor (4), a second gas ejection port (7) for ejecting a nitrogen-containing gas at the predetermined angle with respect to the direction of the axis of rotation of the revolving susceptor (4), and a third gas ejection port (8) for ejecting an inert gas from between the first gas ejection port (6) and the second gas ejection port (7) and at the predetermined angle with respect to the direction of the axis of rotation of the revolving susceptor (4); and an exhaust means (5) for exhausting gas. A group III nitride substrate manufacturing method according to the present invention can be performed by using the manufacturing apparatus of the present invention. According to the present invention, it is possible to provide a manufacturing apparatus and method which can produce a uniform, good group III nitride crystal substrate.